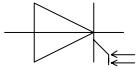

Netz-Thyristor
Phase Control Thyristor
T4003N
Elektrische Eigenschaften / Electrical properties
 Höchstzulässige Werte / Maximum rated values

Periodische Rückwärts-Spitzensperrspannung repetitive peak and reverse voltages	$T_{vj} = -40^{\circ}\text{C} \dots T_{vj \max}$	V_{RRM}	5200	V V
Periodische Rückwärts-Spitzensperrspannung repetitive peak reverse voltages	$T_{vj} = 0^{\circ}\text{C} \dots T_{vj \max}$	V_{RRM}	5400	V V
Durchlaßstrom-Grenzeffektivwert maximum RMS on-state current		I_{TRMSM}	7510	A
Dauergrenzstrom average on-state current	$T_C = 85^{\circ}\text{C}$ $T_C = 60^{\circ}\text{C}$	I_{TAVM}	3410 4780	A A
Stoßstrom-Grenzwert surge current	$T_{vj} = 25^{\circ}\text{C}, t_p = 10 \text{ ms}$ $T_{vj} = T_{vj \max}, t_p = 10 \text{ ms}$	I_{TSM}	105000 100000	A A
Grenzlastintegral I^2t -value	$T_{vj} = 25^{\circ}\text{C}, t_p = 10 \text{ ms}$ $T_{vj} = T_{vj \max}, t_p = 10 \text{ ms}$	I^2t	55000 50000	$10^3 \text{ A}^2\text{s}$ $10^3 \text{ A}^2\text{s}$
Kritische Stromsteilheit critical rate of rise of on-state current	DIN IEC 60747-6 $f = 50 \text{ Hz}, P_{LM} = 40\text{mW}, t_{rise} = 0,5\mu\text{s}$	$(di_T/dt)_{cr}$	300	A/ μs
Kritische Spannungssteilheit critical rate of rise of off-state voltage	$T_{vj} = T_{vj \max}, v_D = 0,67 V_{DRM}$ 5.Kennbuchstabe / 5 th letter H	$(dv_D/dt)_{cr}$	2000	V/ μs

Charakteristische Werte / Characteristic values

Schutzzündspannung (statisch) Protective break over voltage	$T_{vj} = 0^{\circ}\text{C} \dots T_{vj \max}$ Typischer Degradationsfaktor ist 0,16%/K für $T_{vj} = 0^{\circ}\text{C} \dots 25^{\circ}\text{C}$ Typical de-rating factor of 0,16%/K is applicable for $T_{vj} = 0^{\circ}\text{C} \dots 25^{\circ}\text{C}$	V_{BO}	min. 5200	V
Durchlaßspannung on-state voltage	$T_{vj} = T_{vj \max}, i_T = 6000\text{A}, v_D = 100\text{V}$	v_T	typ. 1,67 max. 1,80	V V
Schleusenspannung threshold voltage	$T_{vj} = T_{vj \max}$	$V_{(TO)}$	typ. 0,82 max. 0,92	V V
Ersatzwiderstand slope resistance	$T_{vj} = T_{vj \max}$	r_T	typ. 0,139 max. 0,142	m Ω m Ω
Durchlaßkennlinie on-state characteristic $v_T = A + B \cdot i_T + C \cdot \ln(i_T + 1) + D \cdot \sqrt{i_T}$	$T_{vj} = T_{vj \max}$	typ.	A 0,2501 B 0,00009213 C 0,0499 D 0,00565	
		max.	A 1,1919 B 0,0000226 C -0,1375 D 0,02157	
minimale Zündlichtleistung minimum gate trigger light power	$T_{vj} = 25^{\circ}\text{C}, v_D = 100\text{V}$	I_{GT}	max. 40	mW
Haltestrom holding current	$T_{vj} = 25^{\circ}\text{C}$	I_H	max. 100	mA
Einraststrom latching current	$T_{vj} = 25^{\circ}\text{C}, v_D = V,$ $P_{LM} = 40\text{mW}, t_{rise} = 0,5\mu\text{s}$	I_L	max. 1	A
Rückwärts-Sperrstrom reverse blocking current	$T_{vj} = T_{vj \max}$ $v_R = V_{RRM}$	i_R	max. 900	mA
Zündverzug gate controlled delay time	DIN IEC 60747-6 $T_{vj} = 25^{\circ}\text{C}, v_D = 1000\text{V},$ $P_{LM} = 40\text{mW}, t_{rise} = 0,5\mu\text{s}$	t_{gd}	max. 5	μs

prepared by: J. Schneider		date of publication: 29.06.04
approved by: R. Keller		revision: 6


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Elektrische Eigenschaften / Electrical properties
 Charakteristische Werte / Characteristic values

Freiwerdezeit circuit commutated turn-off time	$T_{vj} = T_{vj\ max}$, $i_{TM} = I_{TAVM}$ $V_{RM} = 100\ V$, $v_{DM} = 0,67\ V_{DRM}$ $dv_D/dt = 20\ V/\mu s$, $-di_T/dt = 10\ A/\mu s$ 4.Kennbuchstabe / 4 th letter O	t_q	typ. 500	μs
Sperrverzögerungsladung recovered charge	$T_{vj} = T_{vj\ max}$ $i_{TM} = I_{TAVM}$, $-di_T/dt = 10\ A/\mu s$ $V_R = 0,5V_{RRM}$, $V_{RM} = 0,8V_{RRM}$	Q_r	max. 28	mAs
Rückstromspitze peak reverse recovery current	$T_{vj} = T_{vj\ max}$ $i_{TM} = I_{TAVM}$, $-di_T/dt = 10\ A/\mu s$ $V_R = 0,5V_{RRM}$, $V_{RM} = 0,8V_{RRM}$	I_{RM}	max. 600	A

Thermische Eigenschaften / Thermal properties

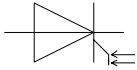
Innerer Wärmewiderstand thermal resistance, junction to case	<u>Kühlfläche / cooling surface</u> beidseitig / two-sided, $\theta = 180^\circ\ sin$ beidseitig / two-sided, DC Anode / anode, DC Kathode / cathode, DC	R_{thJC}	max. 0,0048 max. 0,0045 max. 0,0083 max. 0,0101	$^\circ C/W$ $^\circ C/W$ $^\circ C/W$ $^\circ C/W$
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	<u>Kühlfläche / cooling surface</u> beidseitig / two-sided einseitig / single-sided	R_{thCH}	max. 0,001 max. 0,002	$^\circ C/W$ $^\circ C/W$
Höchstzulässige Sperrschichttemperatur maximum junction temperature		$T_{vj\ max}$	120	$^\circ C$
Betriebstemperatur operating temperature		$T_{c\ op}$	-40...+120	$^\circ C$
Lagertemperatur storage temperature		T_{stg}	-40...+150	$^\circ C$

Mechanische Eigenschaften / Mechanical properties

Gehäuse, siehe Anlage case, see annex			Seite 3 page 3	
Si-Element mit Druckkontakt Si-pellet with pressure contact				
Anpresskraft clamping force		F	90...130	kN
Gewicht weight		G	typ. 4000	g
Kriechstrecke creepage distance			49	mm
Schwingfestigkeit vibration resistance	f = 50 Hz		50	m/s ²

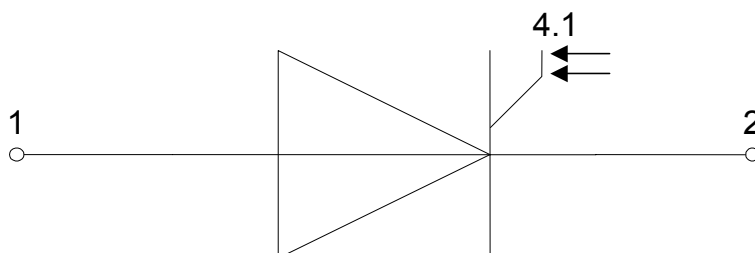
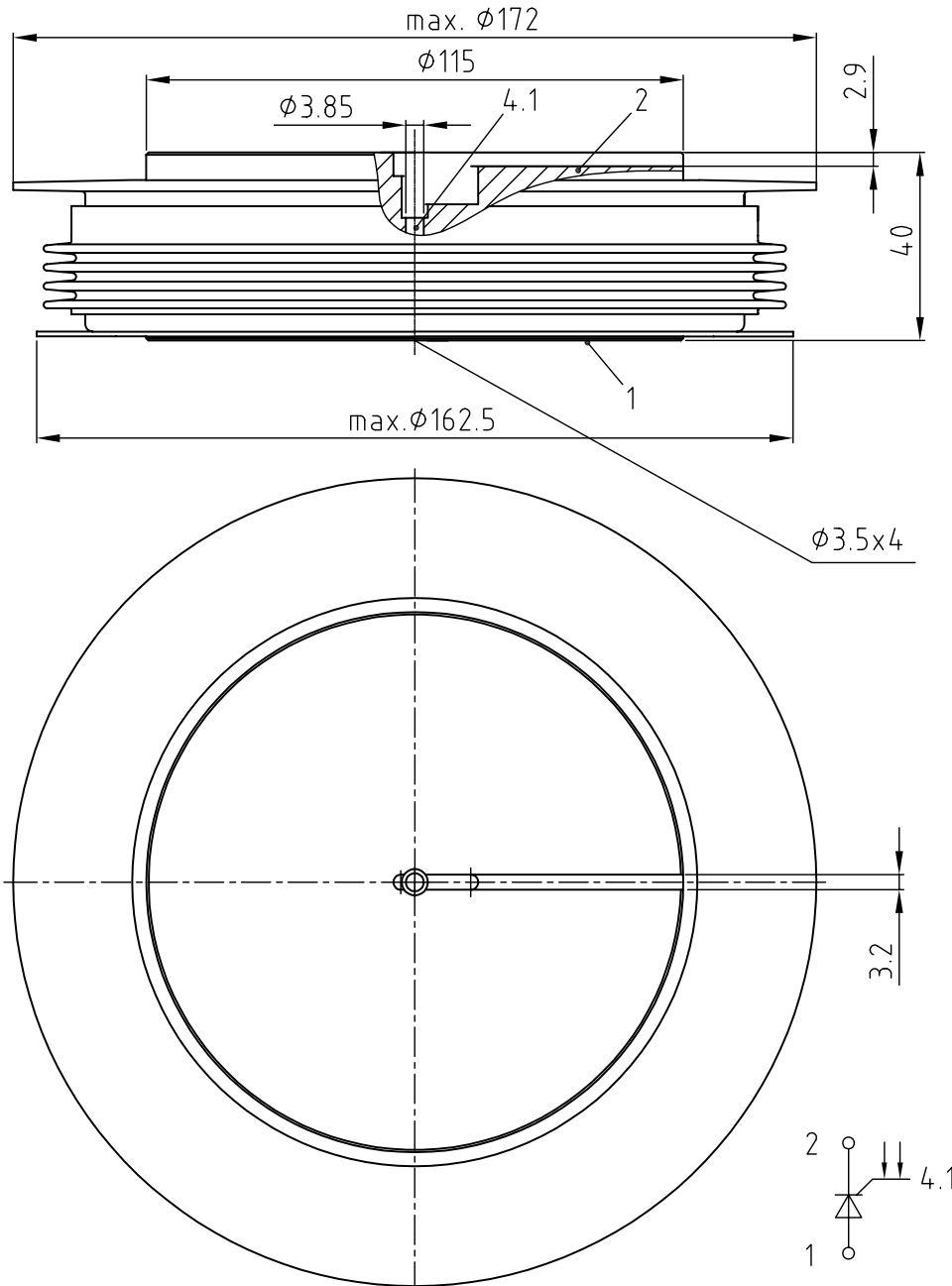
Mit diesem Datenblatt werden Halbleiterbauelemente spezifiziert, jedoch keine Eigenschaften zugesichert. Sie gilt in Verbindung mit den zugehörigen technischen Erläuterungen.

This data sheet specifies semiconductor devices, but promises no characteristics. It is valid in combination with the belonging technical notes.

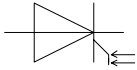


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- 1:** Anode/Anode
- 2:** Kathode/Cathode
- 4.1:** Gate



Netz-Thyristor
Phase Control Thyristor

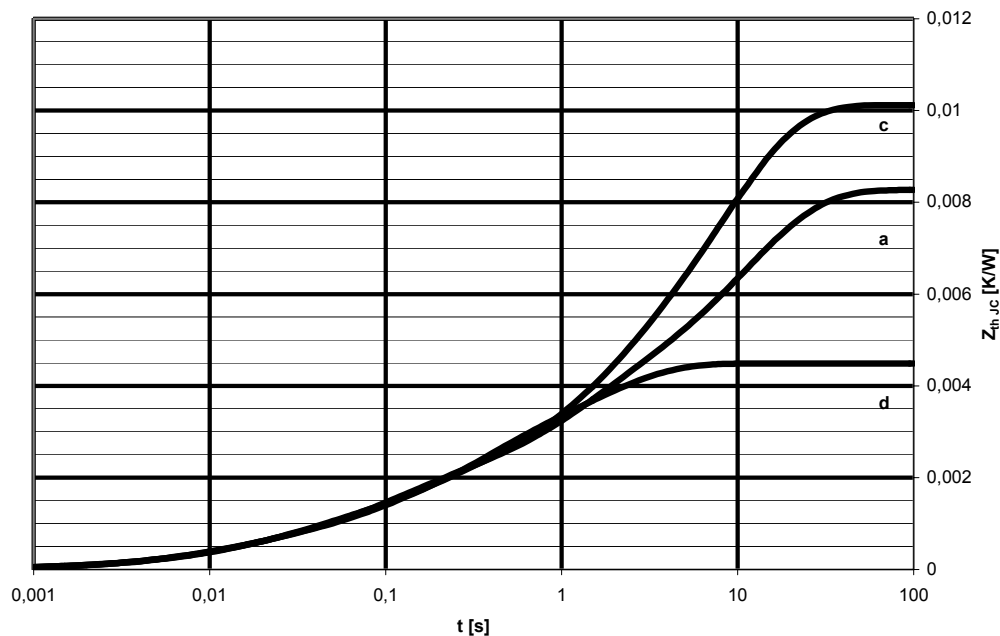
T4003N

Analytische Elemente des transienten Wärmewiderstandes Z_{thJC}
Analytical elements of transient thermal impedance Z_{thJC}

	Pos. n	1	2	3	4	5	6	7
beidseitig two-sided	R_{thn} [°C/W]	0,00206	0,0016	0,00076	0,00007			
	τ_n [s]	1,6	0,27	0,026	0,0047			
anodenseitig anode-sided	R_{thn} [°C/W]	0,0047	0,00188	0,00131	0,00038			
	τ_n [s]	11,2	1,0565	0,09265	0,01079			
kathodenseitig cathode-sided	R_{thn} [°C/W]	0,00674	0,00168	0,00124	0,00046			
	τ_n [s]	8,35	1,242	0,1124	0,0119			

Analytische Funktion / Analytical function:

$$Z_{thJC} = \sum_{n=1}^{n_{max}} R_{thn} \left(1 - e^{-\frac{t}{\tau_n}} \right)$$

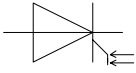


Transienter innerer Wärmewiderstand für DC/ Transient thermal impedance $Z_{thJC} = f(t)$ for DC

Beidseitige Kühlung / Two-sided cooling

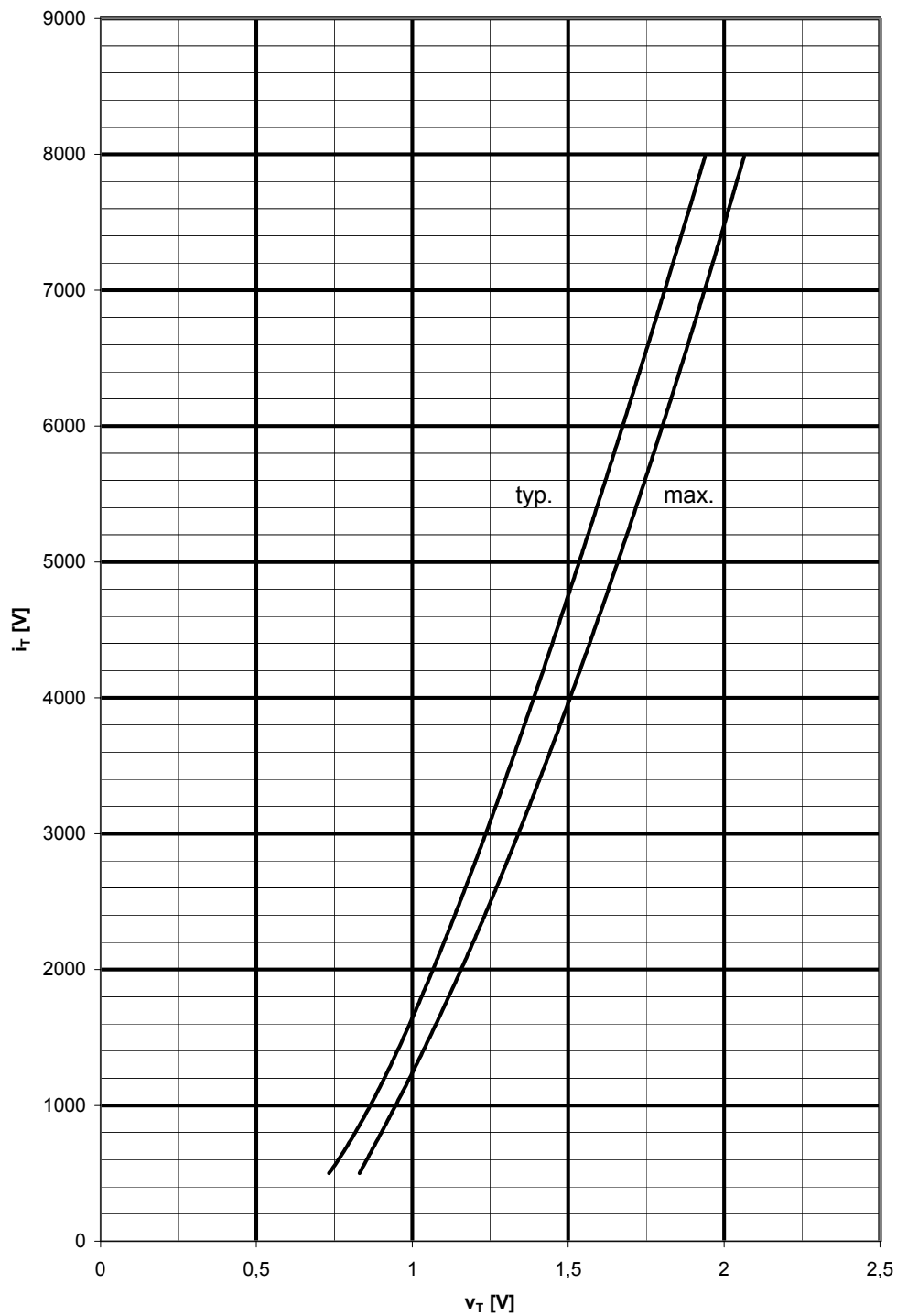
Anodenseitige Kühlung / Anode-sided cooling

Kathodenseitige Kühlung / Cathode-sided cooling



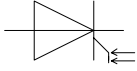
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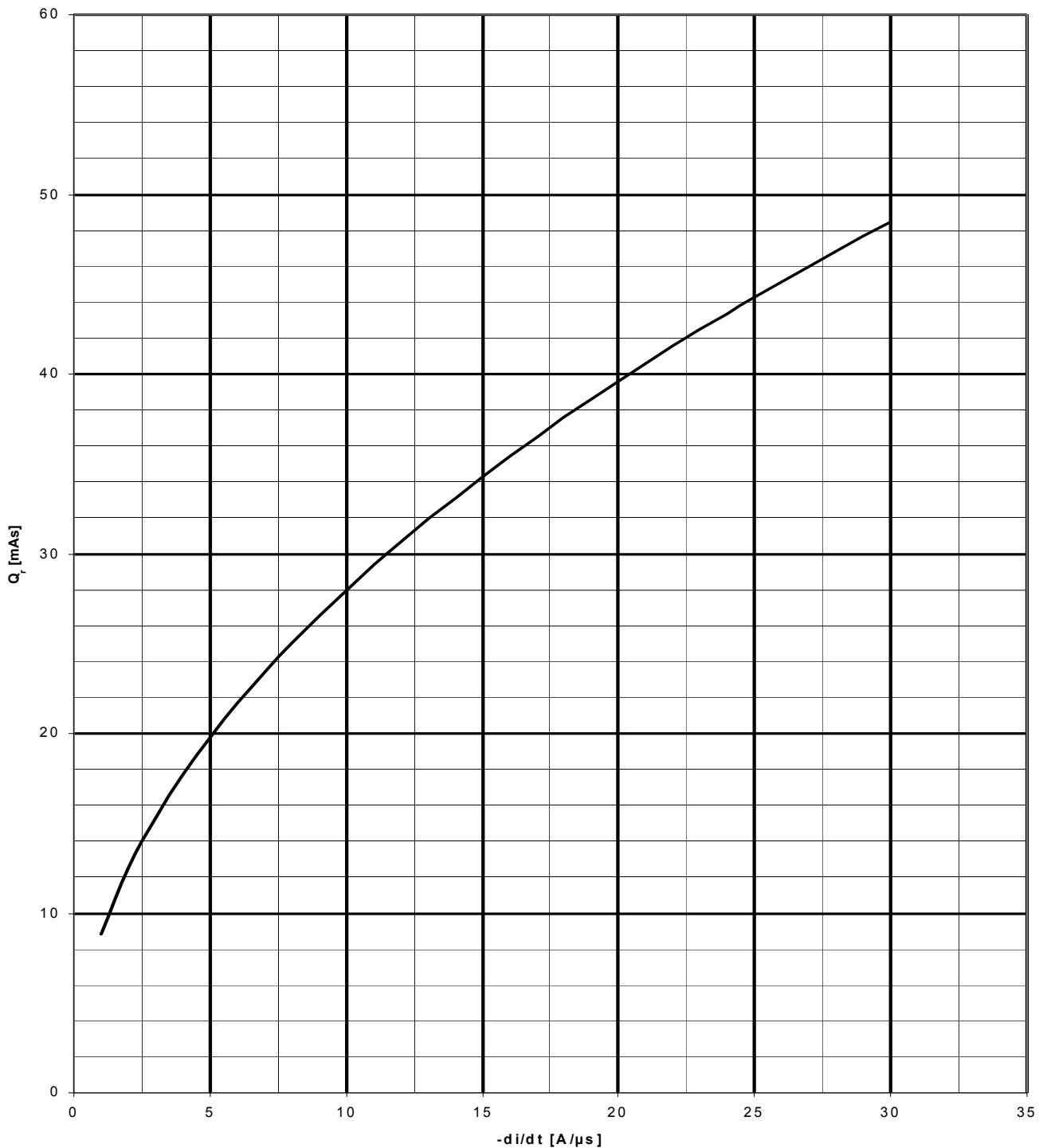
Grenzdurchlaßkennlinie / Limiting on-state characteristic $i_T = f(v_T)$

$$T_{vj} = T_{vj \text{ max}}$$



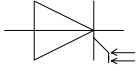
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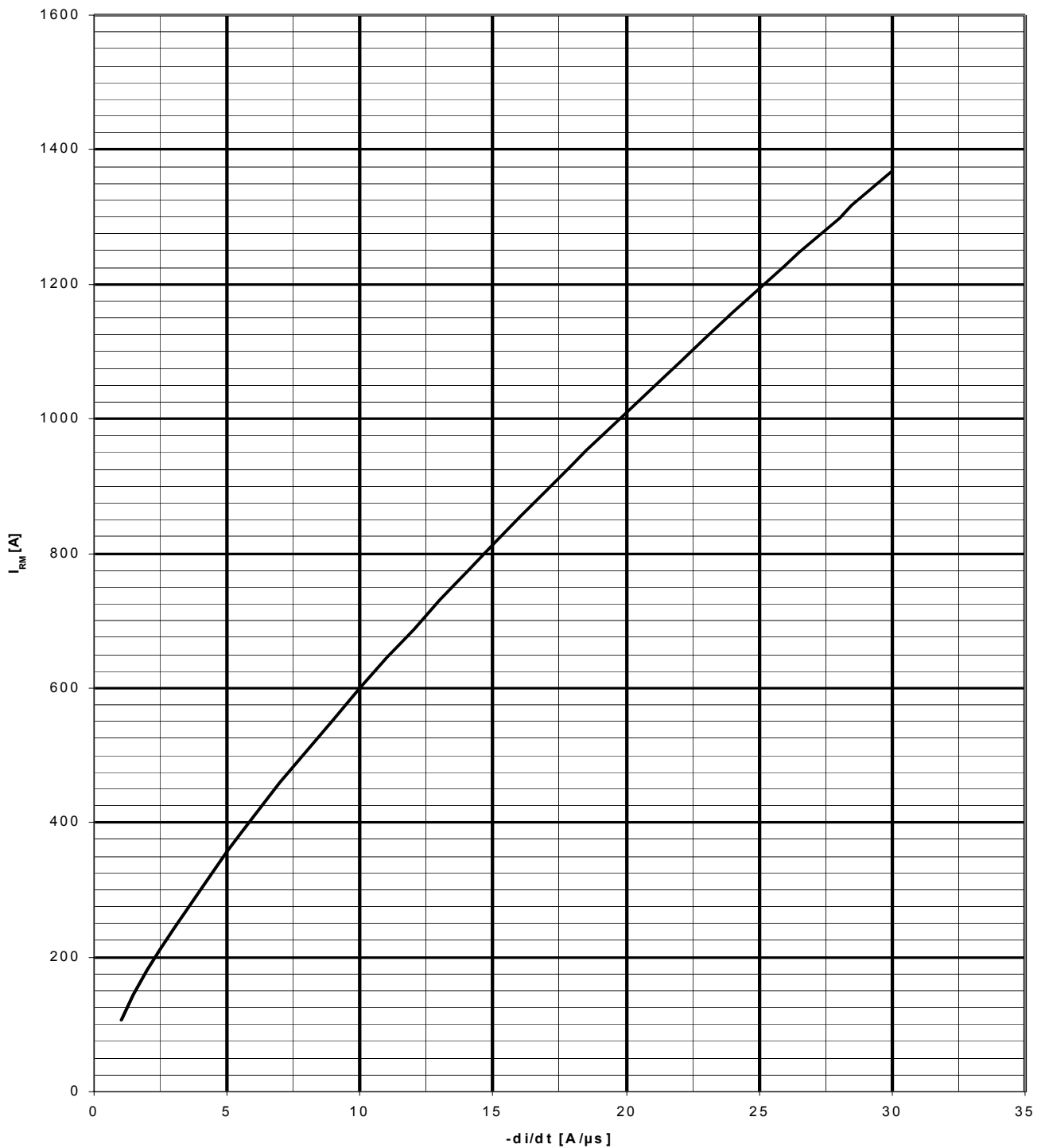
Sperrverzögerungsladung / Recovered charge $Q_r = f(-di/dt)$

$$T_{vj} = T_{vjmax}, V_R = 0,5 V_{RRM}, V_{RM} = 0,8 V_{RRM}$$



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Rückstromspitze / Peak reverse recovery current $I_{RM} = f(-di/dt)$

$$T_{vj} = T_{vjmax}, V_R = 0,5 V_{RRM}, V_{RM} = 0,8 V_{RRM}$$

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